



October 2015

# FDN86501LZ

## N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET 60 V, 2.6 A, 116 mΩ

### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 116 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 2.6\text{ A}$
- Max  $r_{DS(on)}$  = 173 mΩ at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 2.1\text{ A}$
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

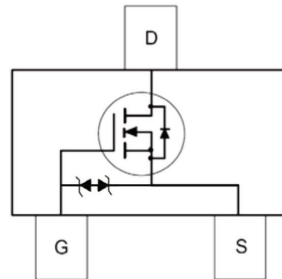
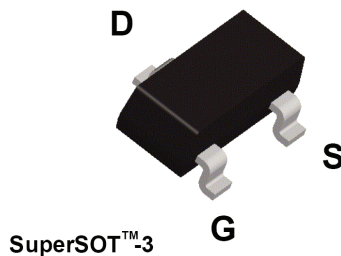


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that incorporates Shielded Gate technology. This process has been optimized for  $r_{DS(on)}$ , switching performance and ruggedness.

### Applications

- Primary DC-DC Switch
- Load Switch



### MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted.

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	-Continuous	(Note 1a) 2.6	A
	-Pulsed	(Note 4) 24	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3) 6	mJ
$P_D$	Power Dissipation	(Note 1a) 1.5	W
	Power Dissipation	(Note 1b) 0.6	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1) 75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a) 80	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
8650	FDN86501LZ	SSOT-3	7"	8 mm	3000 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		68		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.0	1.9	2.4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 2.6\text{ A}$		89	116	m $\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 2.1\text{ A}$		121	173	
		$V_{GS} = 10\text{ V}, I_D = 2.6\text{ A}, T_J = 125\text{ }^\circ\text{C}$		152	198	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 2.6\text{ A}$		8		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		236	335	pF
$C_{oss}$	Output Capacitance			77	110	pF
$C_{rss}$	Reverse Transfer Capacitance			4.9	10	pF
$R_g$	Gate Resistance		0.1	0.8	2.0	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 2.6\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		4.4	10	ns	
$t_r$	Rise Time			1.2	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			9.6	20	ns	
$t_f$	Fall Time			1.2	10	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{ V to } 10\text{ V}$		3.8	5.4	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to } 4.5\text{ V}$	$V_{DD} = 30\text{ V},$ $I_D = 2.6\text{ A}$		1.9	2.7	nC
$Q_{gs}$	Gate to Source Gate Charge				0.7		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				0.6		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.6\text{ A}$ (Note 2)		0.9	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_F = 2.6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		31	50	ns
$Q_{rr}$	Reverse Recovery Charge			19	31	nC

#### Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $80\text{ }^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $180\text{ }^\circ\text{C/W}$  when mounted on a minimum pad.

2. Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle < 2.0%.

3.  $E_{AS}$  of 6 mJ is based on starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 3\text{ mH}$ ,  $I_{AS} = 2\text{ A}$ ,  $V_{DD} = 60\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 9\text{ A}$ .

4. Pulsed  $I_d$  please refer to Fig 11 SOA graph for more details.

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

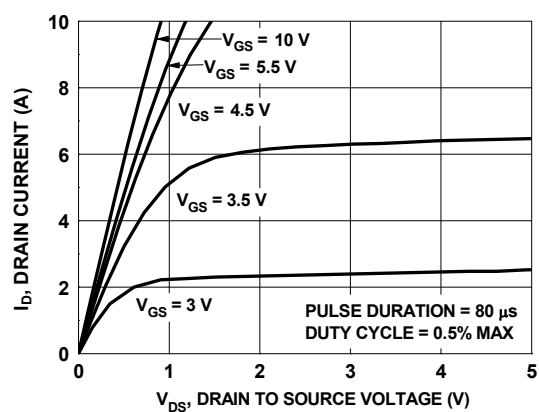


Figure 1. On Region Characteristics

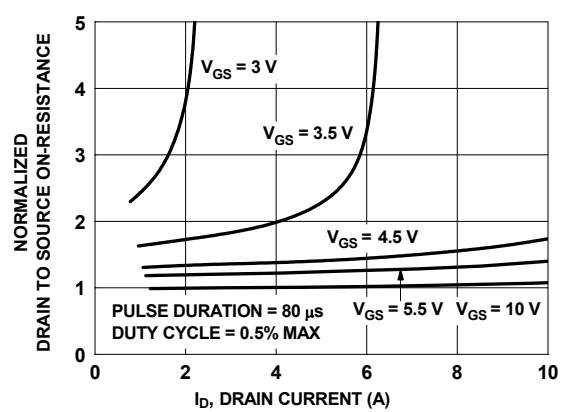


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

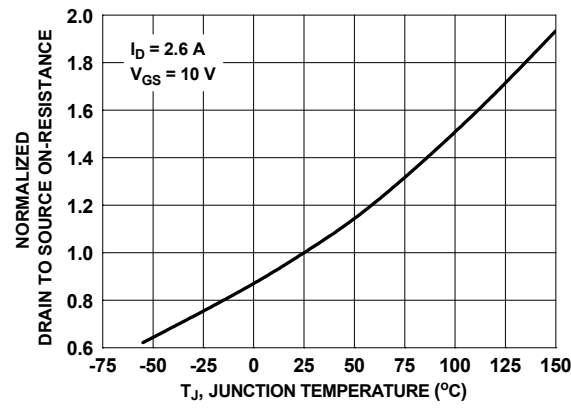


Figure 3. Normalized On Resistance vs. Junction Temperature

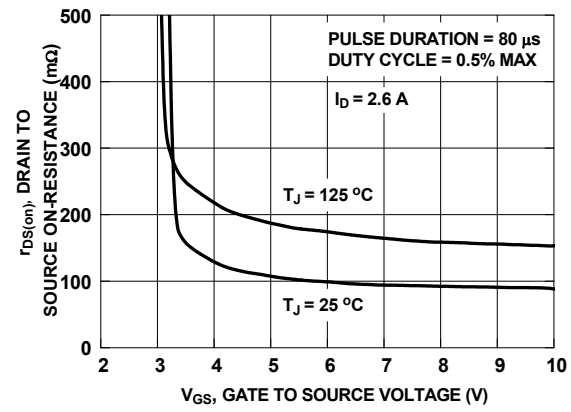


Figure 4. On-Resistance vs. Gate to Source Voltage

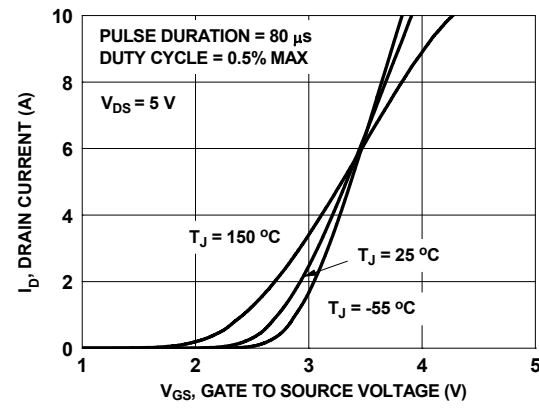


Figure 5. Transfer Characteristics

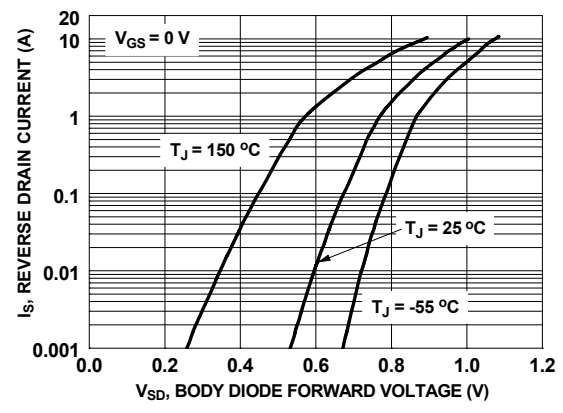
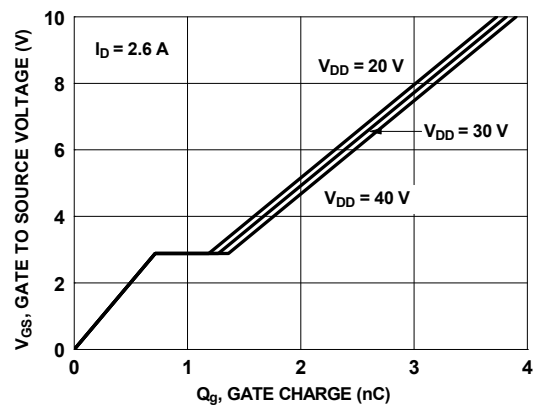
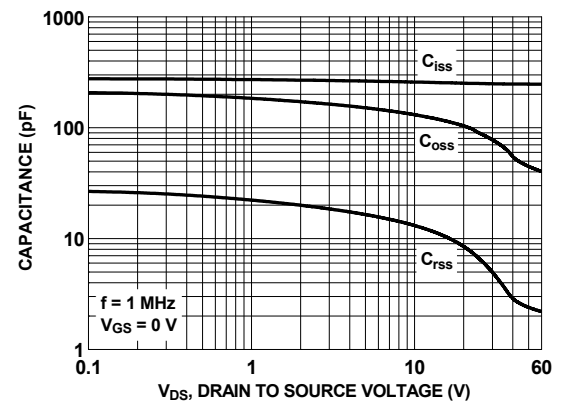


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

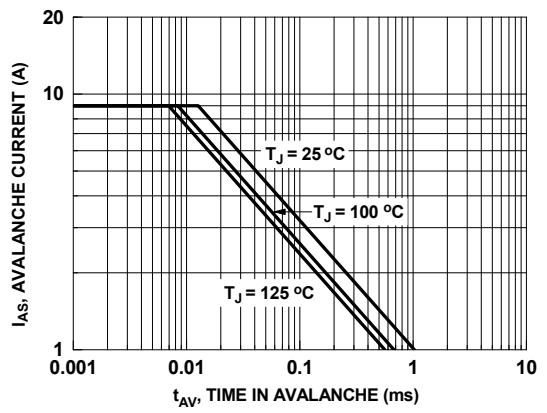
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.



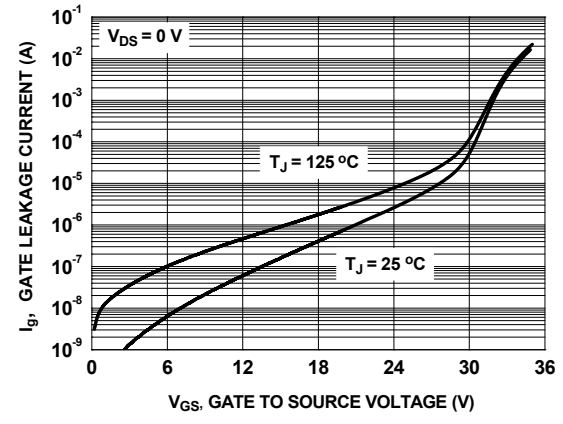
**Figure 7. Gate Charge Characteristics**



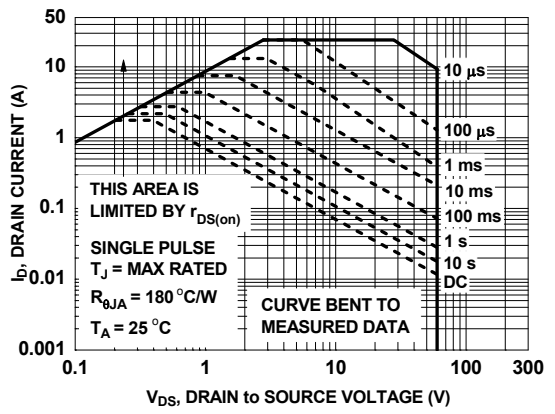
**Figure 8. Capacitance vs. Drain to Source Voltage**



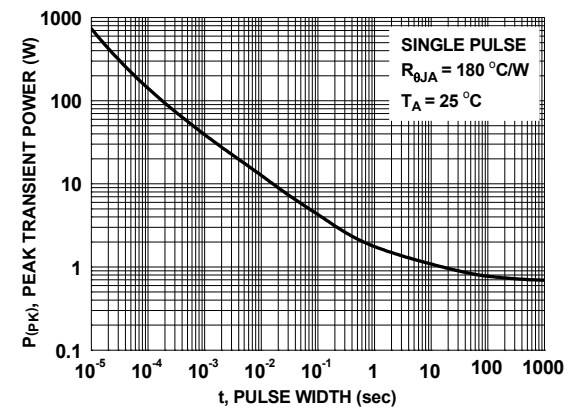
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Gate Leakage Current vs. Gate to Source Voltage**



**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

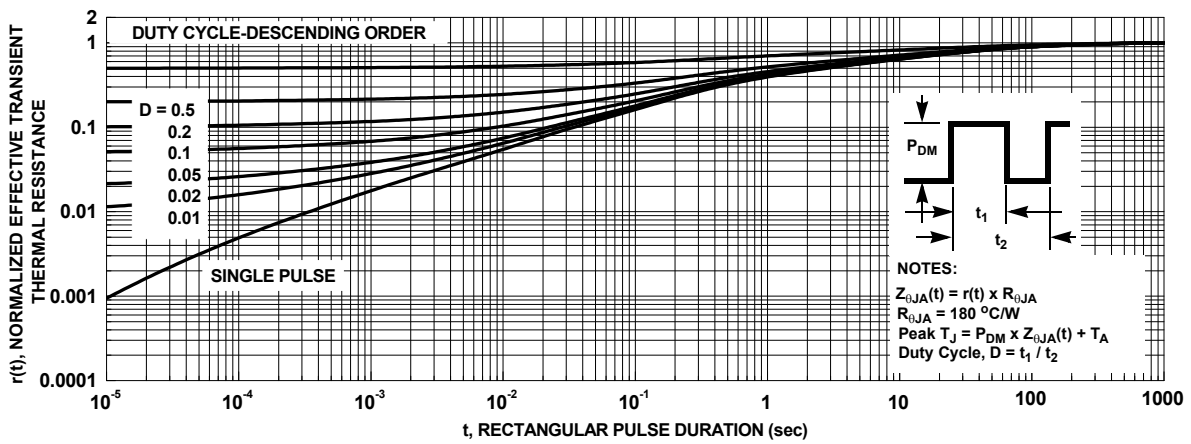
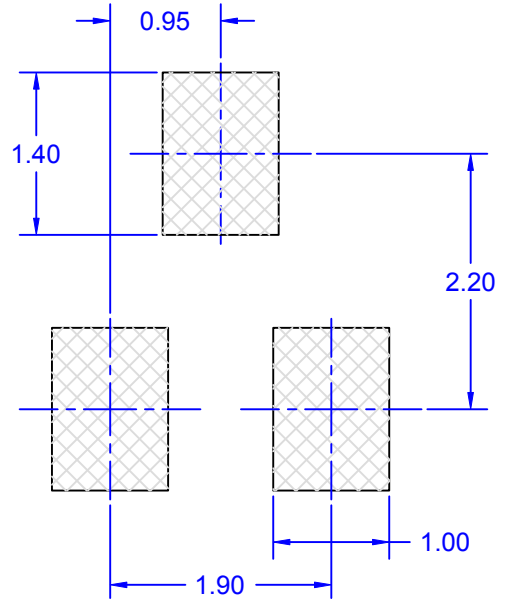
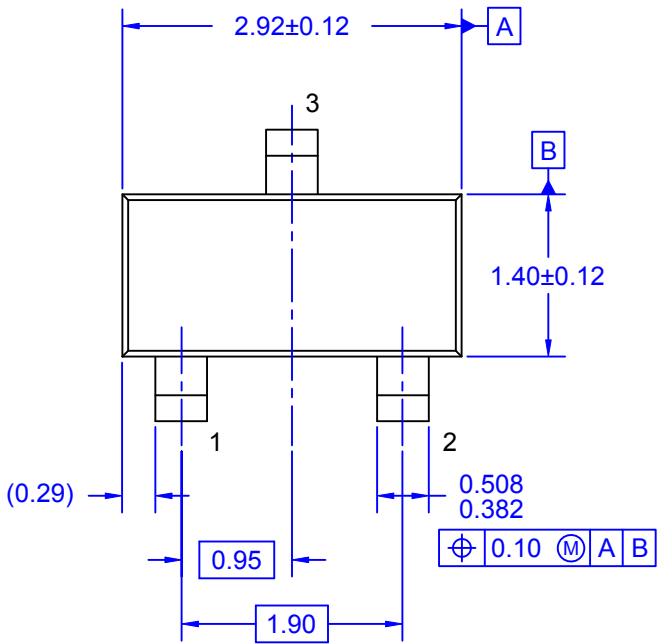
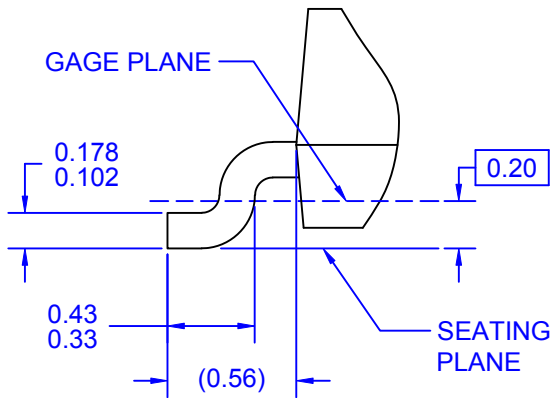
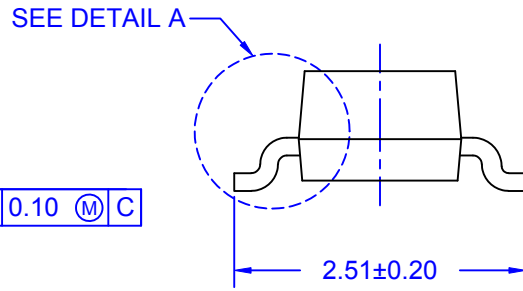
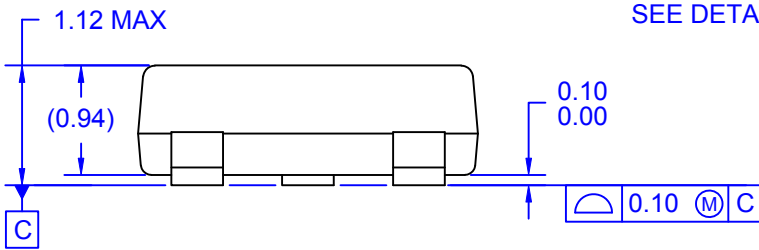


Figure 13. Junction-to-Ambient Transient Thermal Response Curve



LAND PATTERN RECOMMENDATION



**DETAIL A**

SCALE: 50:1

NOTES: UNLESS OTHERWISE SPECIFIED

- A) NO JEDEC REFERENCE AS OF AUGUST 2003
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
- E) DRAWING FILE NAME: MKT-MA03BREV3



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